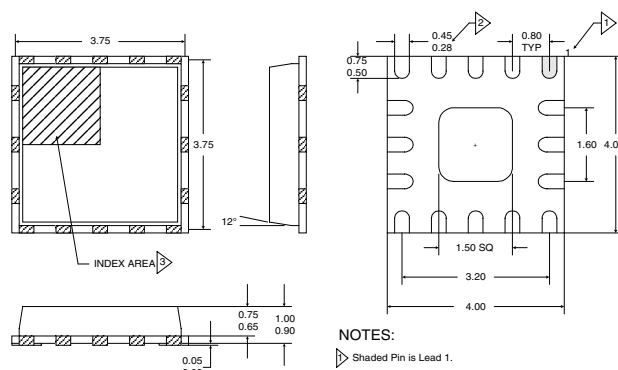


Typical Applications

- 3V CDMA/AMPS Cellular Handsets
- 3V JCDMA/TACS Cellular Handsets
- 3V TDMA/AMPS Cellular Handsets
- Spread Spectrum Systems
- CDPD Portable Data Cards
- Portable Battery-Powered Equipment

Product Description

The RF2162 is a high-power, high-efficiency linear amplifier IC targeting 3V handheld systems. The device is manufactured on an advanced Gallium Arsenide Hetero-junction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in dual-mode 3V CDMA/AMPS hand-held digital cellular equipment, spread spectrum systems, and other applications in the 800MHz to 960MHz band. The RF2162 has an analog bias control voltage to maximize efficiency. The device is self-contained with 50Ω input and the output can be easily matched to obtain optimum power, efficiency, and linearity characteristics. The device is packaged in a compact 4mmx4mm MLF (micro leaded package).



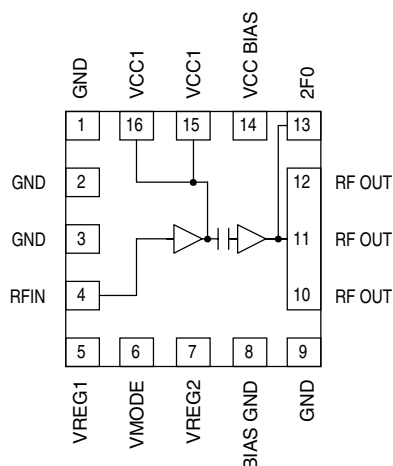
Dimensions in mm.

NOTES:

- ▶ Shaded Pin is Lead 1.
- ▶ Dimension applies to plated terminal and is measured between 0.10 mm and 0.25 mm from terminal tip.
- ▶ The terminal #1 identifier and terminal numbering convention shall conform to JESD 95-1 SPP-012. Details of terminal #1 identifier are optional, but must be located within the zone indicated. The identifier may be either a mold or marked feature.
- 4 Pins 1 and 9 are fused.
- 5 Package Warpage: 0.05 max.

Optimum Technology Matching® Applied

- ☐ Si BJT ☒ GaAs HBT ☐ GaAs MESFET
☐ Si Bi-CMOS ☐ SiGe HBT ☐ Si CMOS



Functional Block Diagram

Package Style: MLF16

Features

- Single 3V Supply
- 29dBm Linear Output Power
- 29dB Linear Gain
- 35% Linear Efficiency
- On-board Power Down Mode
- 800MHz to 960MHz Operation

Ordering Information

- RF2162 3V 900MHz Linear Amplifier
 RF2162 PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc.
7625 Thorndike Road
Greensboro, NC 27409, USA

Tel (336) 664 1233
Fax (336) 664 0454
<http://www.rfmd.com>

Absolute Maximum Ratings

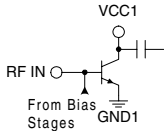
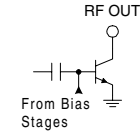
Parameter	Rating	Unit
Supply Voltage (RF off)	+8.0	V _{DC}
Supply Voltage (P _{OUT} ≤31 dBm)	+4.5	V _{DC}
Mode Voltage (V _{MODE})	+3.0	V _{DC}
Control Voltage (V _{PD})	+3.0	V _{DC}
Input RF Power	+12	dBm
Operating Case Temperature	-30 to +110	°C
Storage Temperature	-30 to +150	°C
Moisture Sensitivity	Modified JEDEC Level 2	



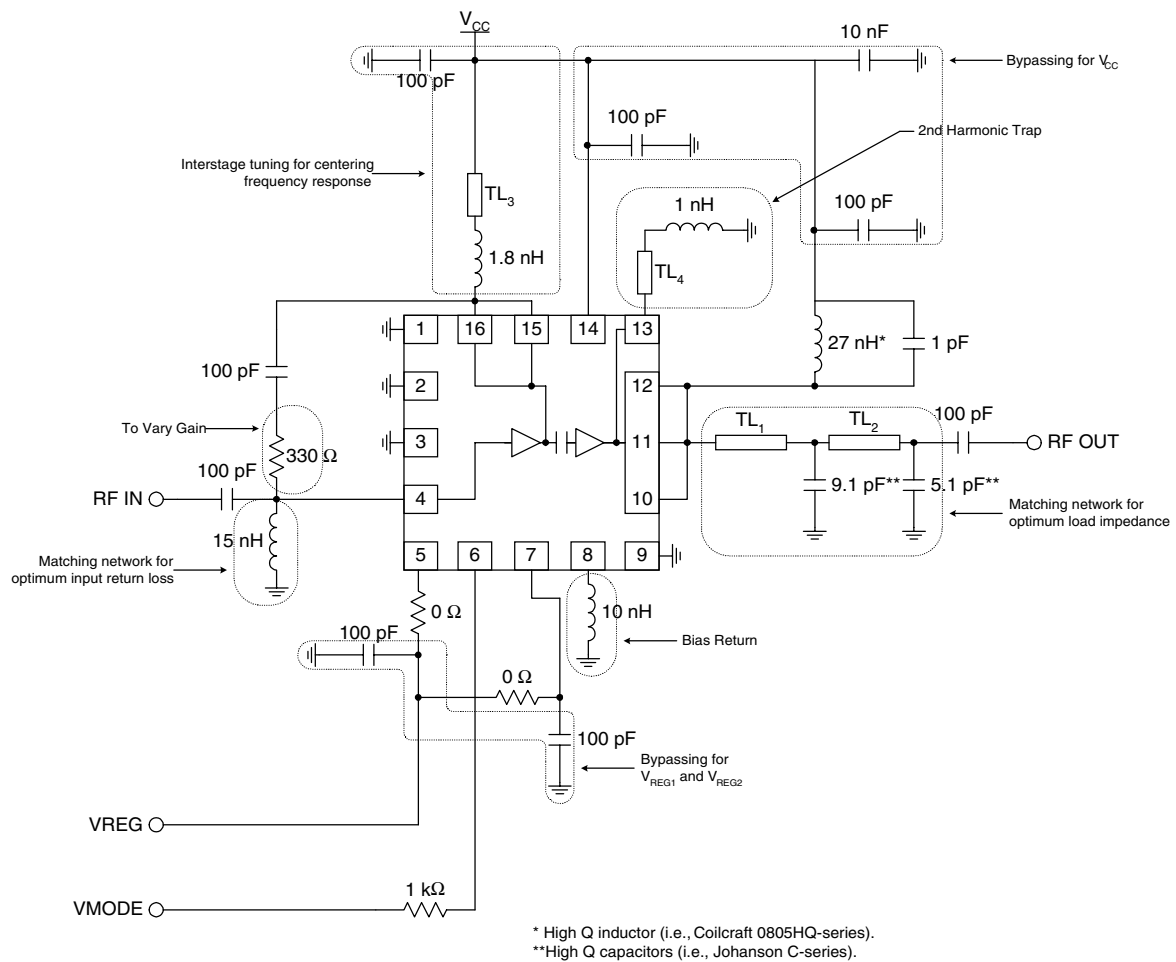
Caution! ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

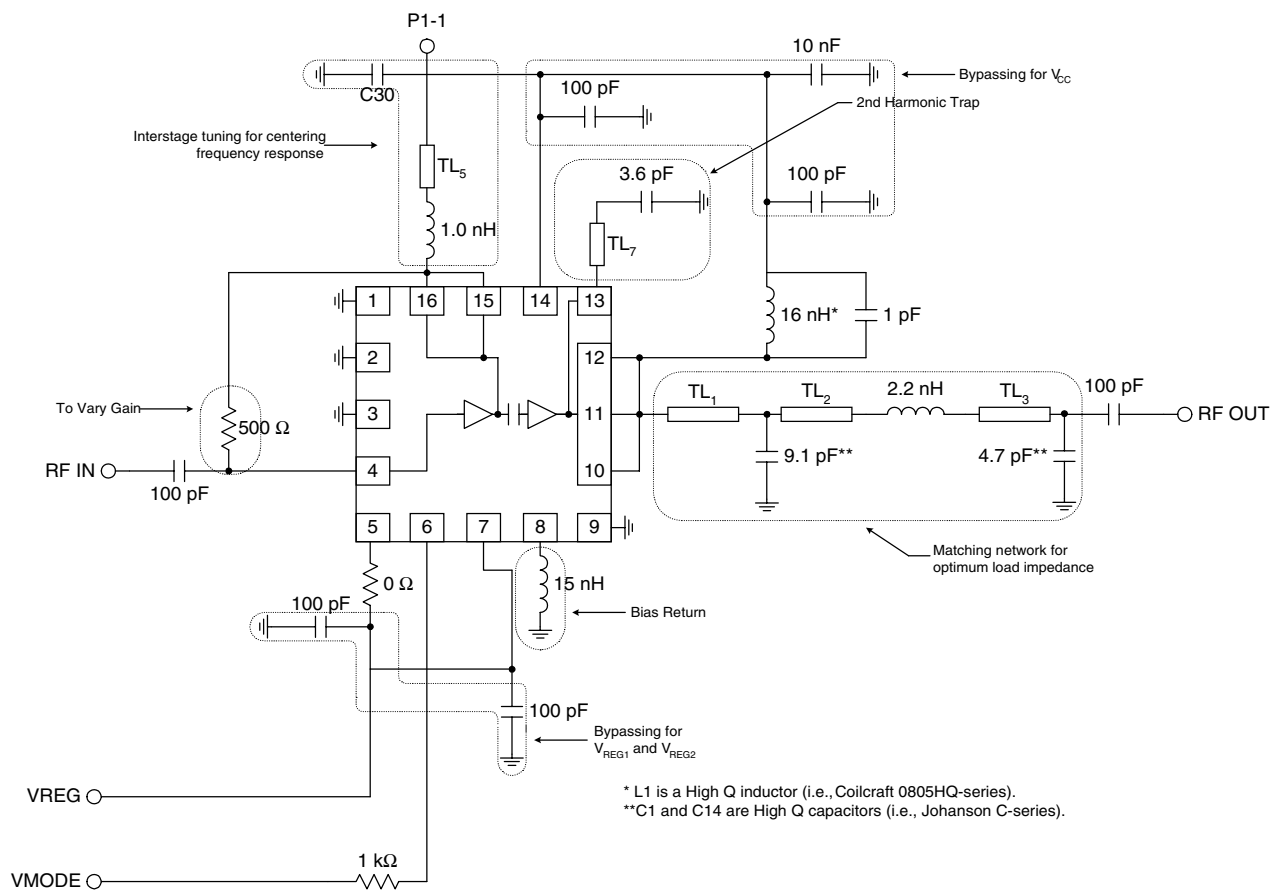
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					T=25°C, V _{CC} =3.4V, Freq=824MHz to 849MHz unless otherwise specified
Usable Frequency Range	800		960	MHz	
Typical Frequency Range		824-849		MHz	
Linear Gain	28	29	31	dB	
Second Harmonic (including second harmonic trap)		-30		dBc	
Max CW Output Power		31.5		dBm	
Total Efficiency (AMPS mode)		50		%	
Maximum Linear Output Power (CDMA Modulation)		29		dBm	
Total Linear Efficiency	30	35		%	
Adjacent Channel Power Rejection		-46	-44	dBc	ACPR @ 885kHz
Noise Power		-58	-56	dBc	ACPR @ 1980kHz
		-90	-89	dBm	V _{CC} =3.4V; BW=30kHz; RX Band NF measure from TX center band to RX center band.
Maximum Linear Output Power (CDMA Modulation)		29		dBm	V _{CC} =3.0V
Total Efficiency (AMPS mode)		50		%	
Max CW Output Power	30	30.5	31	dBm	
Total Linear Efficiency	30	36		%	
Adjacent Channel Power Rejection		-46	-44	dBc	ACPR @ 885kHz
		-58	-56	dBc	ACPR @ 1980kHz
Input VSWR		<2:1			
Output Load VSWR			10:1		No damage.
Power Supply					
Power Supply Voltage	3.0	3.4	4.5	V	
Idle Current		135	200	mA	V _{MODE} =0V to 0.5V
V _{REG} Current		10	15	mA	Total pins 6 and 7, V _{REG} =2.8V
Turn On/Off time			<100	ns	
Total Current (Power down)			10	μA	V _{PD} =Low
V _{REG} "Low" Voltage		0	0.2	V	
V _{REG} "High" Voltage	2.7	2.8	2.9	V	
V _{MODE} Bias Control Voltage Range		0 to 2.5		V	

Pin	Function	Description	Interface Schematic
1	GND	Ground connection. Connect to package base ground. This ground should be isolated from the backside ground contact on top metal layer.	
2	GND1	Ground for stage 1. Keep traces physically short and connect immediately to ground plane for best performance. This ground should be isolated from the backside ground contact on top metal layer.	
3	GND1	Same as Pin 2.	
4	RF IN	RF input. An external DC blocking capacitor is required if this port is connected to a DC path to ground or a DC voltage.	
5	VREG1	Enable voltage for first stage. When this pin is "low", all circuits are shut off. When this pin is 2.8V, all circuits are operating normally. V_{REG} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V. A 100pF high frequency bypass capacitor is recommended.	
6	VMODE	This is an analog bias current control pin. The range is 0V for minimum bias to 3.0 for maximum bias.	
7	VREG2	Enable voltage for second or output stage. When this pin is "low", all circuits are shut off. When this pin is 2.8V, all circuits are operating normally. V_{REG} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V. A 100pF high frequency bypass capacitor is recommended.	
8	GND	Bias circuitry ground. See application schematic.	
9	GND	Ground connection. Connect to package base ground. This ground should be isolated from the backside ground contact on top metal layer.	
10	RF OUT	RF output and power supply for the output stage. The bias for the output stage is provided through this pin and pin 13. An external matching network is required to provide the optimum load impedance; see the application schematics for details.	
11	RF OUT	Same as pin 10.	See pin 10.
12	RF OUT	Same as pin 10.	
13	2FO	Harmonic trap. This pin connects to the RF output but is used for providing a low impedance to the second harmonic of the operating frequency. An inductor or transmission line resonating with an on chip capacitor at 2fo is required at this pin.	
14	VCC BIAS	Power supply for bias circuitry. A 100pF high frequency bypass capacitor is recommended.	
15	VCC1	Interstage tuning and bias supply for first stage.	
16	VCC1	Interstage tuning and bias supply for first stage.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

Application Schematic - US CDMA

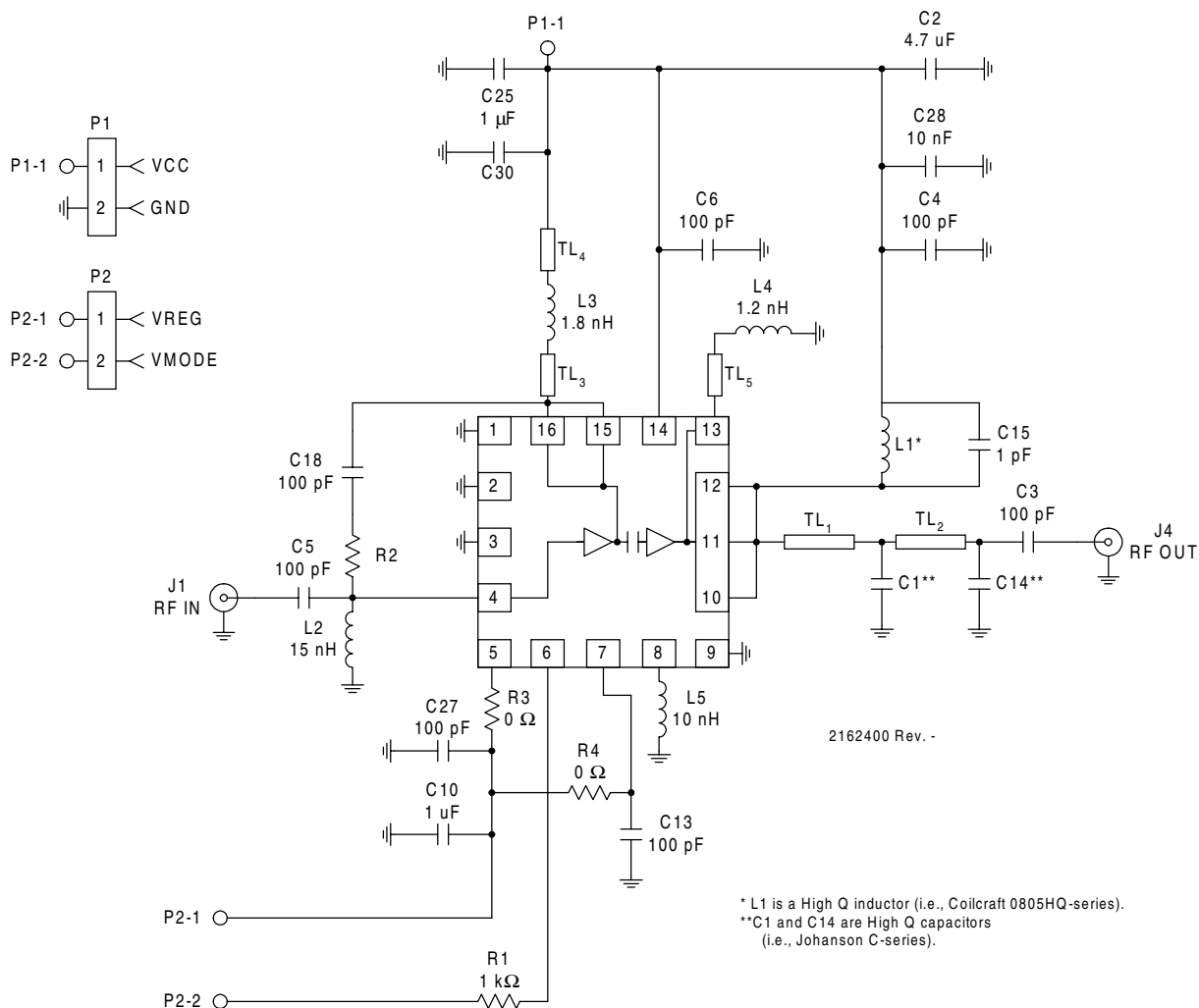


Application Schematic - US TDMA



Evaluation Board Schematic - US CDMA

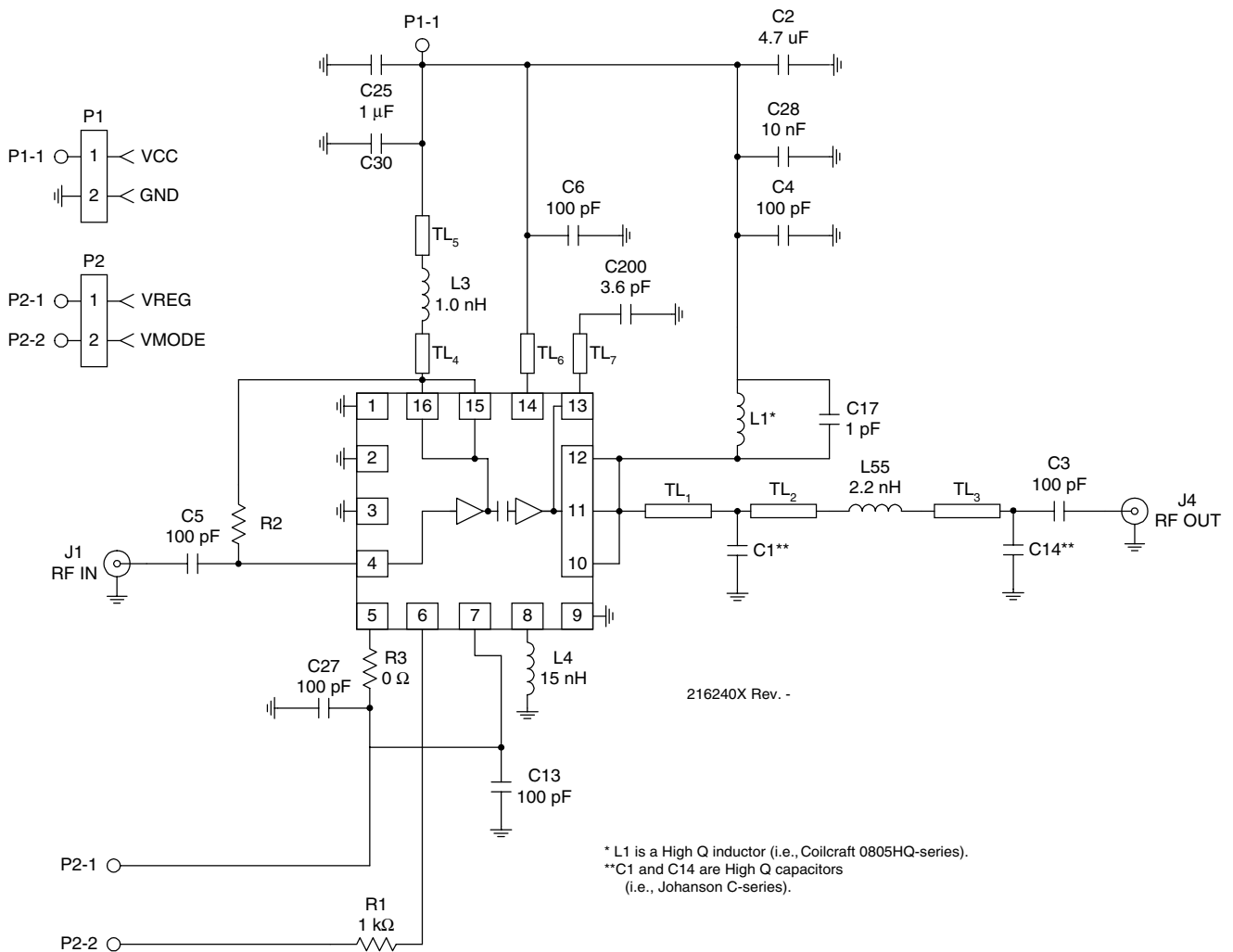
(Download [Bill of Materials](http://www.rfmd.com) from www.rfmd.com.)



Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C14 (pF)
CDMA (US)	330	100	9.1	27	5.1

Transmission Line Length	TL ₁	TL ₂	TL ₃	TL ₄	TL ₅
CDMA (US)	200 mils	150 mils	L=15 mils W=16 mils	L=40-45 mils from L3 W=16 mils	L=15-20 mils W=14 mils

Evaluation Board Schematic - US TDMA



Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C14 (pF)
TDMA (US)	500	56	9.1	16	4.7

Transmission Line Length	TL ₁	TL ₂	TL ₃	TL ₄	TL ₅	TL ₆	TL ₇
TDMA (US)	155 mils	47 mils	L=44 mils	L=12 mils W=16 mils	L=49 mils W=16 mils	L=12 mils	L=12 mils W=14 mils

Evaluation Board Layout 2.0" x 2.0"

Board Thickness 0.031", Board Material FR-4

